



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SMALL FLAT
NPN Epitaxial Transistor**

VOLTAGE 1€0 Volts CURRENT FË Ampere

3N% \$\$' ; D

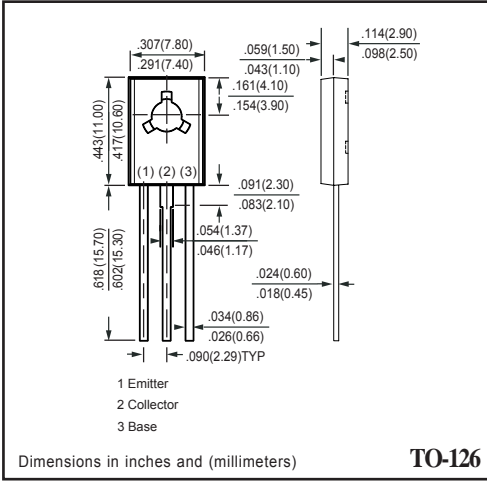
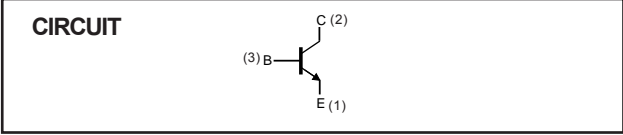
APPLICATION
* Power driver and Dc to DC convertor .

FEATURE
* Small flat package. (TO-126)
* PC= 1.5 W (mounted on ceramic substrate).
* High saturation current capability.

CONSTRUCTION
* NPN Switching Transistor



TO-126



TO-126

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	700	V
V _{CEO}	collector-emitter voltage	open base	–	400	V
V _{EBO}	emitter-base voltage	open collector	–	9	V
I _C	collector current (DC)		–	1.5	A
P _C	Collector power dissipatio		–	1.5	W
T _{stg}	storage temperature		–55	+150	°C
T _j	junction temperature		–	150	°C

ELECTRICAL CHARACTERISTIC (3N13003GP)

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =5mA, I _E =0	700			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =2mA, I _C =0	9			V
Collector cut-off current	I _{CBO}	V _{CB} =700V, I _E =0			1	mA
Collector cut-off current	I _{CEO}	V _{CE} =400V, I _B =0			0.5	mA
Emitter cut-off current	I _{EBO}	V _{EB} =9V, I _C =0			1	mA
DC current gain	h _{FE1}	V _{CE} =5V, I _C = 0.5 A	8		40	
	h _{FE2}	V _{CE} =5V, I _C = 1.5A	5			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A, I _B =0.25A			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =1A, I _B =0.25A			1.2	V
Transition frequency	f _T	V _{CE} =10V, I _C =100mA, f =1MHz	5			MHz
Fall time	t _f	I _C =1A, I _{B1} =-I _{B2} =0.2A, V _{CC} =100V			0.5	μs
Storage time	t _s	I _C =250mA (UI9600)	2		4	μs

RATING CHARACTERISTIC CURVES (3N13003GP)

Typical Electrical Characteristics

